

LH03 Series of Products interconvert:

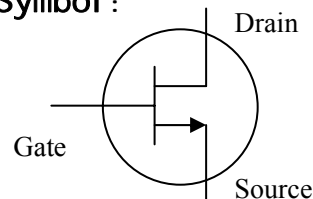
**2SK30A****Silicon N-Channel Junction FET**■ **Application:**

For charge sensor, meter amplifier circuit, rheostat , chopper and gain controller for AGC , electronic switch.

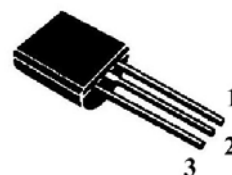
■ **Absolute Maximum Ratings (Ta=25°C)**

Parameter	Symbol	Ratings	Unit
Gate to Drain voltage	V <sub>GD0</sub>	-50	V
Gate to Source voltage	V <sub>GSO</sub>	-50	V
Gate current	I <sub>G</sub>	10	mA
Allowable power dissipation	P <sub>D</sub>	250	mW
Junction Temperature	T <sub>j</sub>	125	°C
Storage Temperature	T <sub>stg</sub>	-55 to +125	°C

Symbol :



Package example:



Package	D	S	G
SC-59			
SOT-23			
TO-92S			
* TO-92	3	1	2
TO-18			

■ **Electrical Characteristics (Ta=25°C)**

Parameter	Symbol	Conditions	min	typ	max	Unit
Drain to Source cut-off current	I <sub>DSS</sub>	V <sub>DS</sub> = 10V, V <sub>GS</sub> = 0V	0.3		6.5	mA
Gate to Source leakage current	I <sub>GSS</sub>	V <sub>GS</sub> = -30V, V <sub>DS</sub> = 0V			-1.0	nA
Gate to Drain voltage	V <sub>GDS</sub>	I <sub>G</sub> = -100μA, V <sub>DS</sub> = 0V	-50			V
Gate to Source cut-off voltage	V <sub>GS(OFF)</sub>	V <sub>DS</sub> = 10V, I <sub>D</sub> = 0.1μA	-0.4		-5.0	V
Forward transfer admittance	Y <sub>fs</sub>	V <sub>DS</sub> = 10V, V <sub>GS</sub> = 0V, f = 1KHZ	1.2			mS
Input capacitance (Common Source)	C <sub>iss</sub>	V <sub>DS</sub> = 10V, V <sub>GS</sub> = 0V, f = 1MHZ		8.2		pF
Reverse transfer capacitance (Common Source)	C <sub>rss</sub>			2.6		pF

■ **I<sub>DSS</sub> Rank Classification**

Rank	R	O	Y	GR
I <sub>DSS</sub> (mA)	0.3 to 0.75	0.6 to 1.4	1.2 to 3.0	2.6 to 6.5
Marking Symbol	035D	035E	035F	035G

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